

IN THE SPECIFICATION:

The Applicants request that the paragraph beginning at line 21 on page 6 of the written description be amended as follows:

cMUTs are silicon-based devices that comprise small (e.g., 50 μm) capacitive "drumheads" or cells that can transmit and receive ultrasound energy. Referring to FIG. 1, a typical MUT transducer cell 2 is shown in cross section. An array of such MUT transducer cells is typically fabricated on a substrate 4, such as a silicon wafer. For each MUT transducer cell, a thin membrane or diaphragm 8, which may be made of silicon, silicon nitride, or other suitable material, is suspended above the substrate 4. The membrane 8 is supported on its periphery by an insulating support 6, which may be made of silicon, silicon oxide, or silicon nitride. The cavity 15 between the membrane 8 and the substrate 4 may be air- or gas-filled or wholly or partially evacuated. A film or layer of conductive material, such as aluminum alloy or other suitable conductive material, forms an electrode 12 on the membrane 8, and another film or layer made of conductive material forms an electrode 10 on the substrate 4. Alternatively, the electrode 10 can be embedded in the substrate 4 or substrate 4 may itself be conductive, such as doped n- or p- type silicon. Also the ~~electrode 12 can be on top of membrane 8 rather than embedded within it as shown in FIG. 1.~~

IN THE DRAWINGS:

The Applicants request that Figure 1 be amended to show electrode 12 on top of the membrane 8 instead of being embedded in the membrane. A Replacement Sheet is submitted herewith.